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REMARKS

Claims 1-7 and 20-22 are currently pending in the subject application and are presently under consideration. Claims 8-19 stand withdrawn. Amendments to the specification to cure minor informalities are at pages 2-4. A version of the claims is found at pages 5-8. Claims 1-3, 6 and 20-22 has been amended herein. Favorable reconsideration of the subject patent application is respectfully requested in view of the comments and amendments herein.

It is noted that the primary reference Oglesby *et al.* (US 6,656,763) is commonly owned by the assignee of the subject application; and the inventors Jane V. Oglesby, Christopher F. Lyons, Ramkumar Subramanian and Minh V. Ngo are the same for the cited patent and the subject application. Moreover, the inventions of the cited reference and the subject application were commonly owned by Advanced Micro Devices at the time the invention(s) were made.

I. Rejection of Claims 1-7, and 20- 22 Under 35 U.S.C. §102(e)

Claims 1-7 and 20-22 stand rejected under 35 U.S.C. §102(e) as being anticipated by Oglesby *et al.* (US 6,656,763) Applicants' representative respectfully requests that this rejection be withdrawn for at least the following reasons. Oglesby *et al.* fails to teach or suggest all limitations of the subject claims.

A single prior art reference anticipates a patent claim only if it *expressly or inherently describes each and every limitation* set forth in the patent claim. *Trintec Industries, Inc. v. Top-U.S.A. Corp.*, 295 F.3d 1292, 63 USPQ2d 1597 (Fed. Cir. 2002); *See Verdegaa Bros. v. Union Oil Co. of California*, 814 F.2d 628, 631, 2 USPQ2d 1051, 1053 (Fed. Cir. 1987). *The identical invention must be shown in as complete detail as is contained in the ... claim.* *Richardson v. Suzuki Motor Co.*, 868 F.2d 1226, 9 USPQ2d 1913, 1920 (Fed. Cir. 1989).

The claimed invention provides for increasing the number of organic memory cells associated with a lithographic feature. In particular, independent claim 1 recites *an array memory formation comprising a first electrode formed from a bit line of the wafer and two second of memory formations associated with lithographic features of a wafer surface, each electrodes in parallel orientation with respect to the first electrode on walls of adjacent lithographic features of the wafer surface.* Independent claims 21 and 22 recite similar

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limitations as claim 1. Oglesby *et al.* is not directed towards such novel features of the subject claims.

Oglesby *et al.* shows a method of forming organic memory cells at bitline and wordline intersections. In this arrangement, bitlines represent the bottom electrode layer of each organic memory cell, while the wordline is representative of a top electrode layer. See Figures 1 and 2. For every bitline, there are intersecting wordlines on the top and bottom thereon.

On page 2 of the subject Office Action, it is incorrectly contended that the electrodes 204 from Figure 2 of the reference equate to the *two electrodes positioned sideways of a first electrode* of the claimed invention. At the indicated portions of Oglesby *et al.*, the two second electrodes to which the Examiner refers are electrode layers which are positioned *in a perpendicular* orientation with respect to a bitline electrode 202. Instead of allowing for memory cells to be formed at the intersections of the perpendicularly oriented electrodes 202 and 204 as in the cited reference, the claimed invention teaches positioning *two second electrodes in parallel orientation with respect to a first electrode* to produce two memory bits for one lithographic feature.

In view of at least the foregoing, it is readily apparent that Oglesby *et al.* does not disclose the identical invention in as much detail as is contained in the subject claims. Accordingly, this rejection with respect to independent claims 1, 20 and 21 (and the claims that depend there from) should be withdrawn.

10/699,903H0416/AMDP949USCONCLUSION

The present application is believed to be in condition for allowance in view of the above comments and amendments. A prompt action to such end is earnestly solicited.

In the event any fees are due in connection with this document, the Commissioner is authorized to charge those fees to Deposit Account No. 50-1063 [AMDP949US].

Should the Examiner believe a telephone interview would be helpful to expedite favorable prosecution, the Examiner is invited to contact applicants' undersigned representative at the telephone number below.

Respectfully submitted,

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